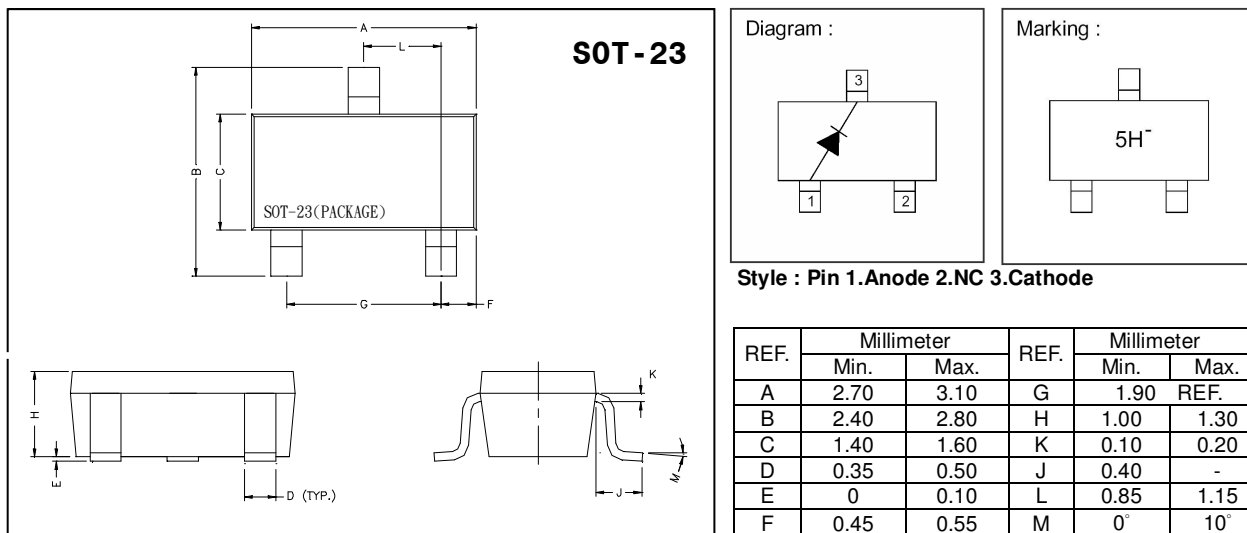


GMBD4148

Description

The GMBD4148 is designed for high-speed switching application in hybrid thick-and thin-film circuits. The devices is manufactured by the silicon epitaxial planar process and packed in plastic surface mount package.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-65~+150	°C
Continuous Reverse Voltage	V _R	70	V
Continuous Forward Current	I _F	200	mA
Peak Forward Surge Current	I _{FSM}	500	mA

Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Forward Voltage	V _F	-	1	V	I _F =10mA
Reverse Breakdown	V _R	100	-	V	I _R =100uA
Reverse Current	I _R	-	5	uA	V _R =75V
Total Capacitance	C _T	-	4	pF	V _R =0V, F=1MHz
Reverse Recovery Time	T _{rr}	-	4	nS	I _F =I _R =10mA, R _L =100Ω Measured at I _R =1mA

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